

Features

- 30V/28A,
 $R_{DS(ON)} = 9m\Omega(Typ.)@V_{GS}=10V$
 $R_{DS(ON)} = 15m\Omega(Typ.)@V_{GS}=4.5V$
- Low $R_{DS(ON)}$
- Super High Dense Cell Design
- Reliable and Rugged

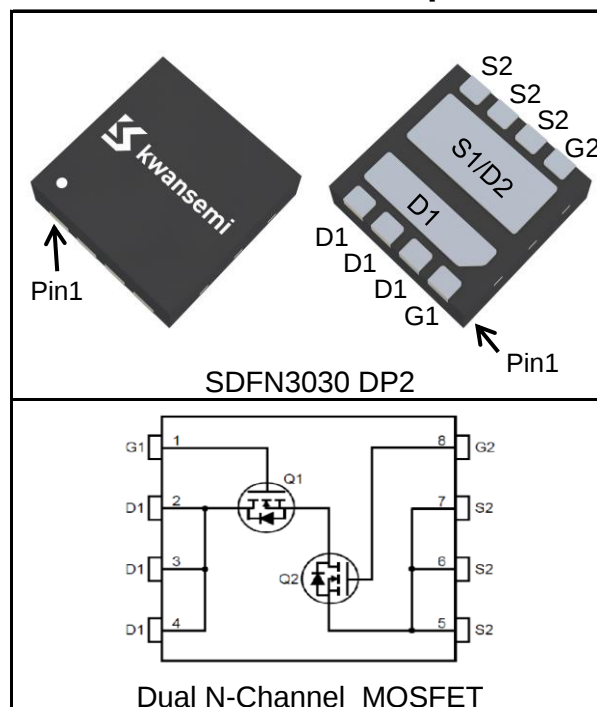
Applications

- DC/DC Converter



Halogen-Free

Pin Description



Absolute Maximum Ratings

Symbol	Parameter		Rating	Unit
Common Ratings (T _C =25°C Unless Otherwise Noted)				
V _{DSS}	Drain-Source Voltage		30	V
V _{GSS}	Gate-Source Voltage		±20	
T _J	Maximum Junction Temperature		150	°C
T _J ,T _{STG}	Operating and Storage Temperature Range		-55 to 150	°C
I _S	Diode Continuous Forward Current	T _C =25°C	28	A
Mounted on Large Heat Sink				
I _{DP} ^①	Pulse Drain Current	T _C =25°C	112	A
I _D ^②	Continuous Drain Current@T _C (V _{GS} =10V)	T _C =25°C	28	A
		T _C =100°C	17	
	Continuous Drain Current@T _A (V _{GS} =10V) ^③	T _A =25°C	11	
		T _A =70°C	9	
P _D	Maximum Power Dissipation@T _C	T _C =25°C	15	W
		T _C =100°C	6	
	Maximum Power Dissipation@T _A ^③	T _A =25°C	2.8	
		T _A =70°C	1.8	

Symbol	Parameter	Rating	Unit
$R_{\theta JC}$	Thermal Resistance-Junction to Case	8	$^{\circ}\text{C/W}$
$R_{\theta JA}^{(3)}$	Thermal Resistance-Junction to Ambient	45	$^{\circ}\text{C/W}$
Drain-Source Avalanche Ratings			
$E_{AS}^{(4)}$	Avalanche Energy, Single Pulsed	42	mJ

Electrical Characteristics ($T_C=25^{\circ}\text{C}$ Unless Otherwise Noted)

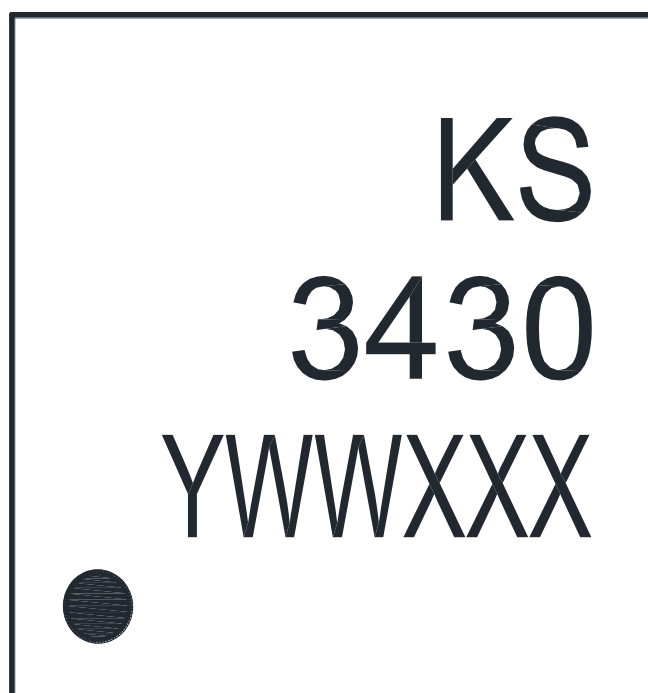
Symbol	Parameter	Test Condition	Rating			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V			1	μA
		T _J =125°C			30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	1.1	1.6	2.3	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V			±100	nA
R _{DS(ON)} ^⑤	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =14A		9	12	mΩ
		V _{GS} =4.5V, I _{DS} =8A		15	20	mΩ
Diode Characteristics						
V _{SD} ^⑤	Diode Forward Voltage	I _{SD} =14A, V _{GS} =0V		0.87	1.2	V
t _{rr}	Reverse Recovery Time	I _{SD} =14A, dI _{SD} /dt=100A/μs		14		ns
Q _{rr}	Reverse Recovery Charge			21		nC
Dynamic Characteristics ^⑥						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz		4.2		Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, Frequency=1.0MHz		705		pF
C _{oss}	Output Capacitance			105		
C _{rss}	Reverse Transfer Capacitance			80		
t _{d(ON)}	Turn-on Delay Time	V _{DD} =15V, I _{DS} =3A, V _{GS} =10V, R _G =6Ω		12		ns
t _r	Turn-on Rise Time			14		
t _{d(OFF)}	Turn-off Delay Time			25		
t _f	Turn-off Fall Time			9		
Gate Charge Characteristics ^⑥						
Q _g	Total Gate Charge	V _{DS} =15V, V _{GS} =10V, I _{DS} =14A		14		nC
Q _{gs}	Gate-Source Charge			2.2		
Q _{gd}	Gate-Drain Charge			3.4		

Notes:

- ①Pulse width limited by safe operating area.
- ②Calculated continuous current based on maximum allowable junction temperature. The package limitation current is 40A.
- ③When mounted on 1 inch square copper board, $t \leq 10\text{sec}$.
- ④Limited by $T_{j\text{max}}$, Starting $T_j = 25^\circ\text{C}$, $I_{AS\text{max}} = 13\text{A}$, $L = 0.5\text{mH}$, $V_{DD} = 20\text{V}$, $R_G = 25\Omega$, $V_{GS} = 10\text{V}$. Part not recommended for use above this value.
- ⑤Pulse test; Pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
- ⑥Guaranteed by design, not subject to production testing.

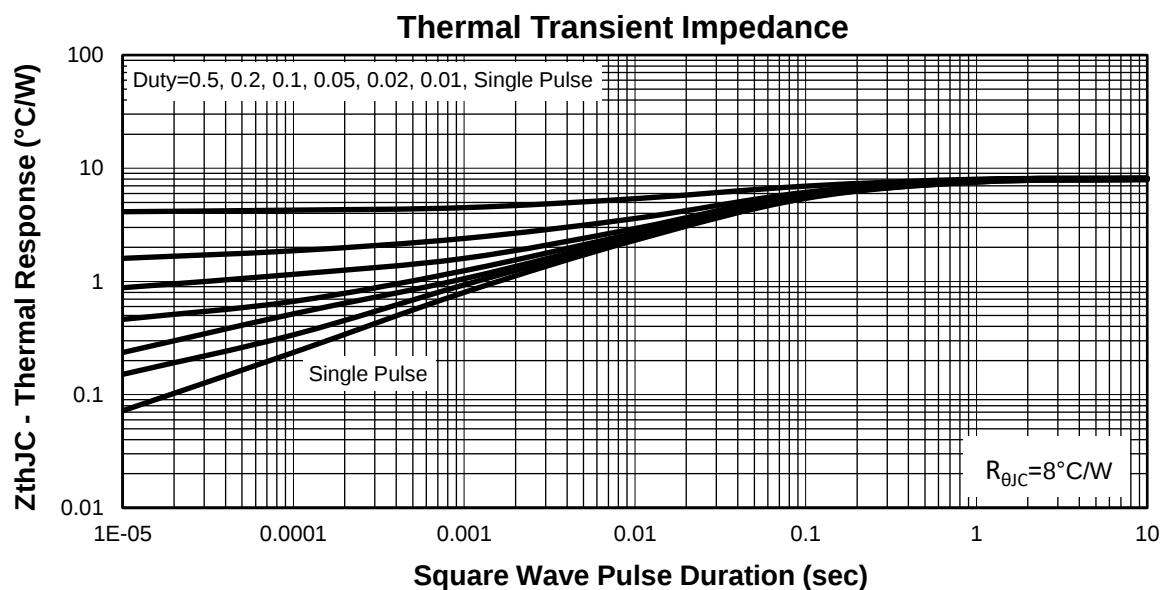
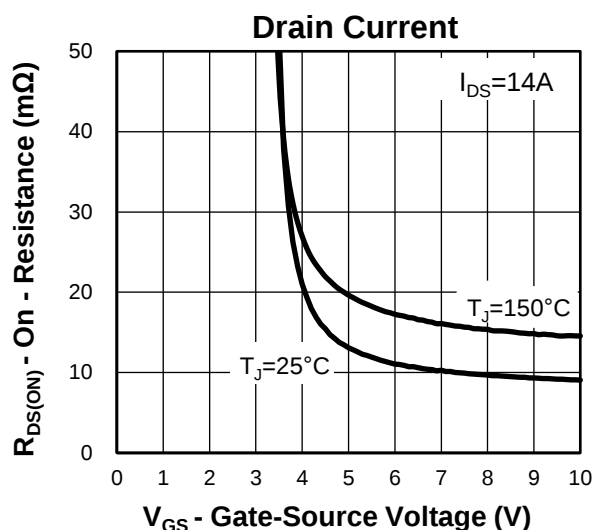
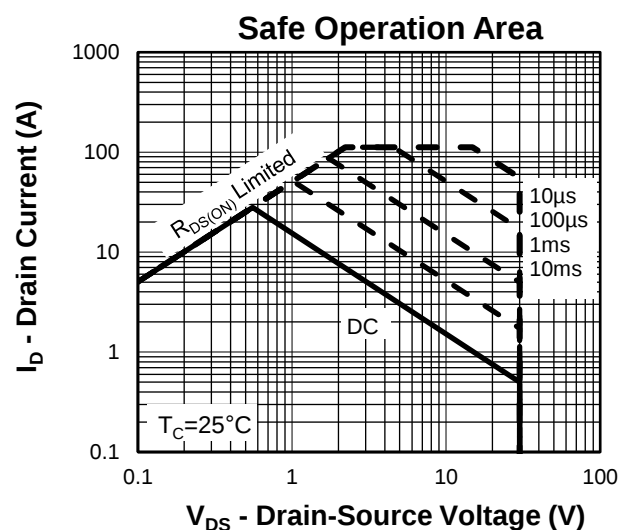
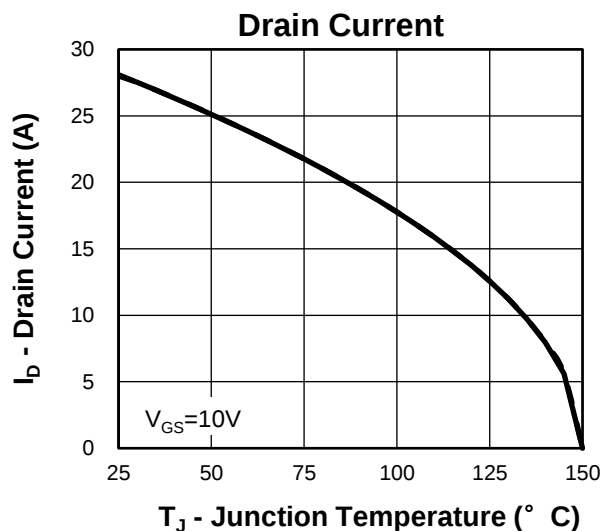
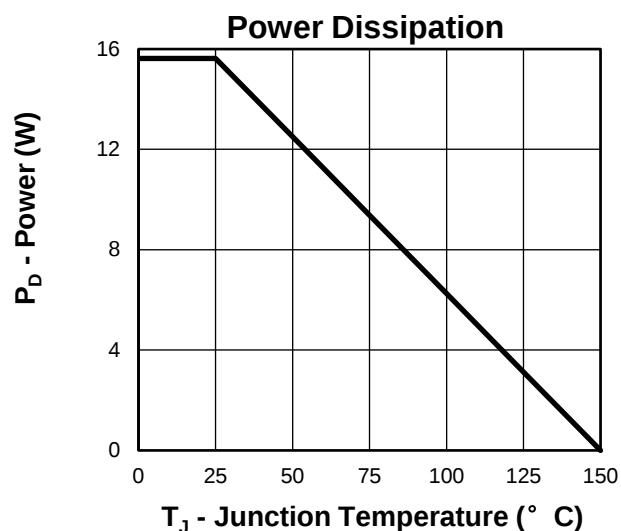
Ordering and Marking Information

Device	Package	Packaging	Quantity	Reel Size	Tape width
KS3430UA3	SDFN3030 DP2	Tape&Reel	5000	13"	12mm

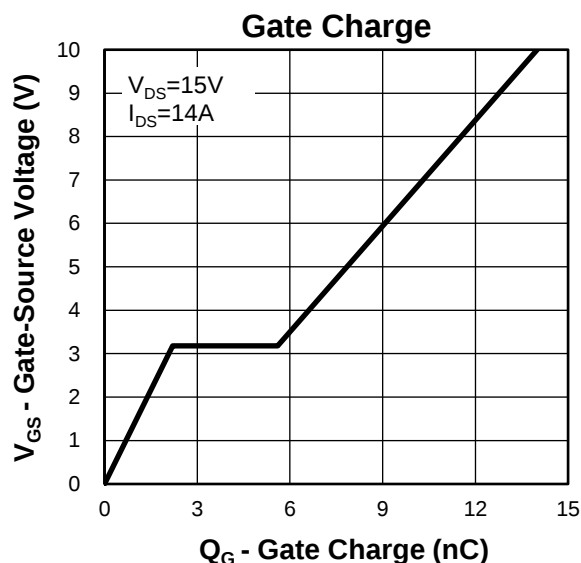
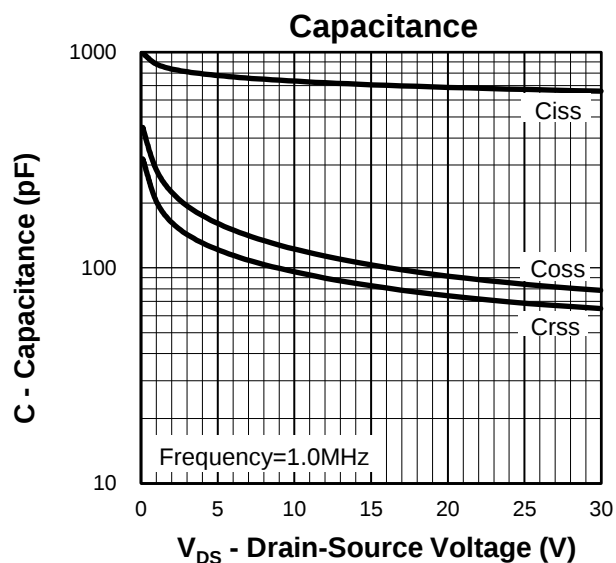
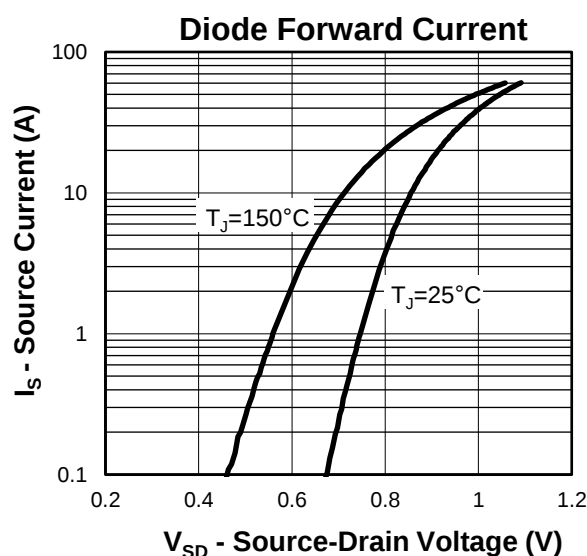
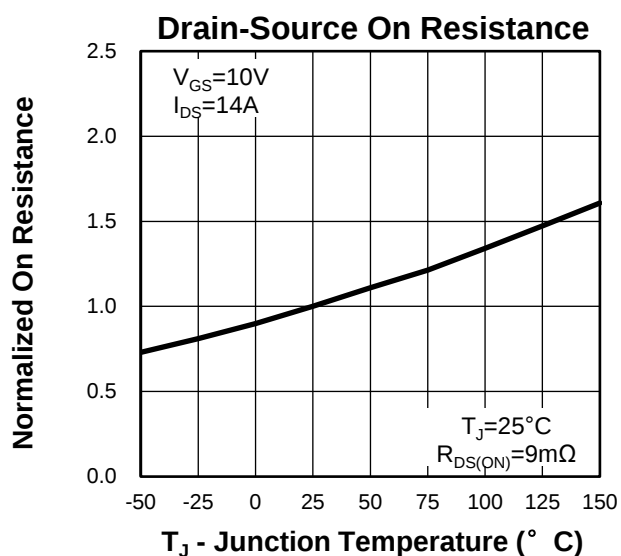
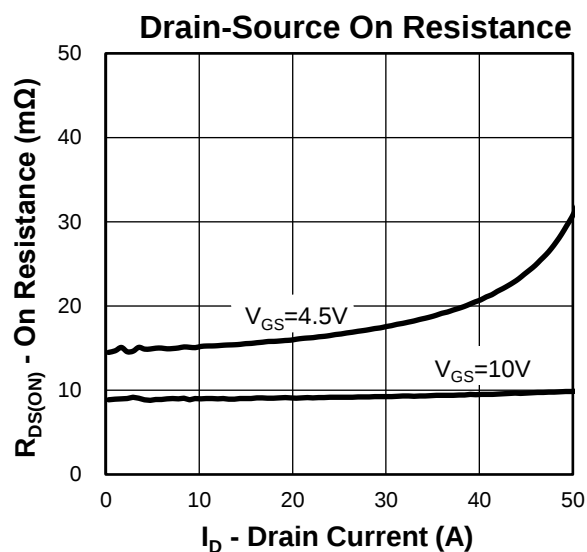
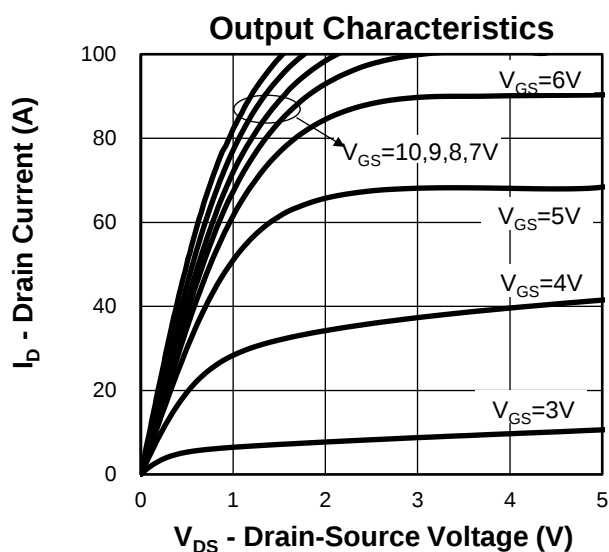


1st Line: Kwansemi Code(KS)
 2nd Line: Part Number(3430)
 3rd Line: Lot Number(YWWXXX)

Typical Characteristics

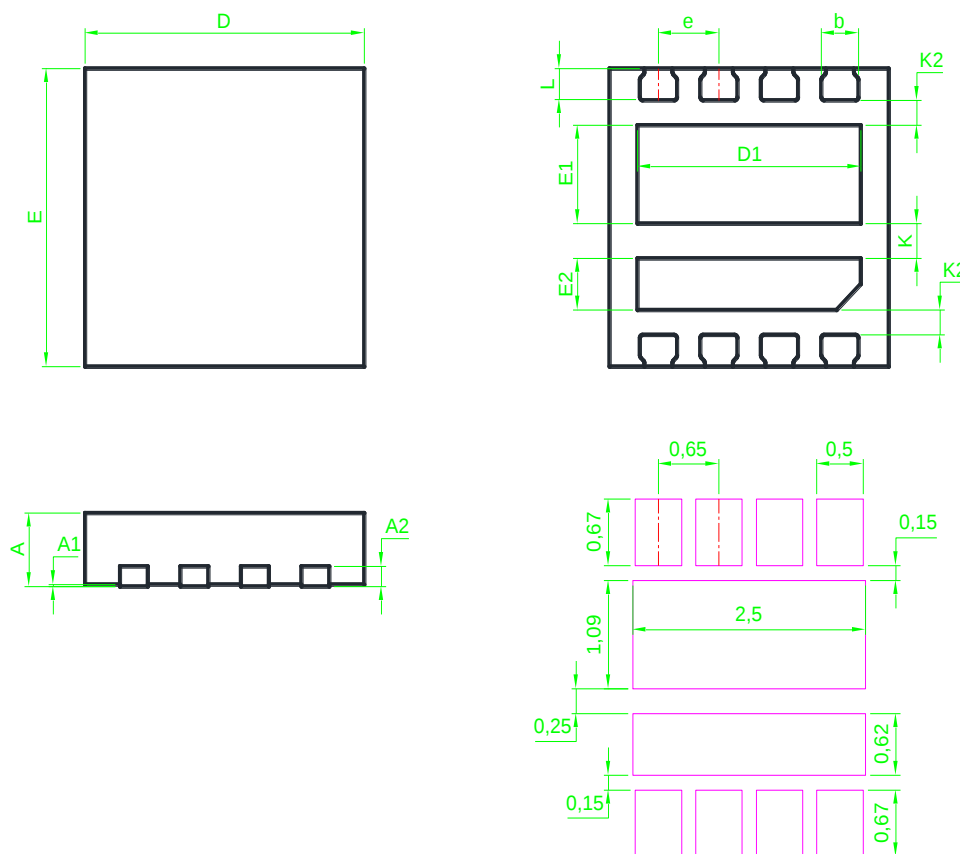


Typical Characteristics



Package Information

SDFN3030 DP2

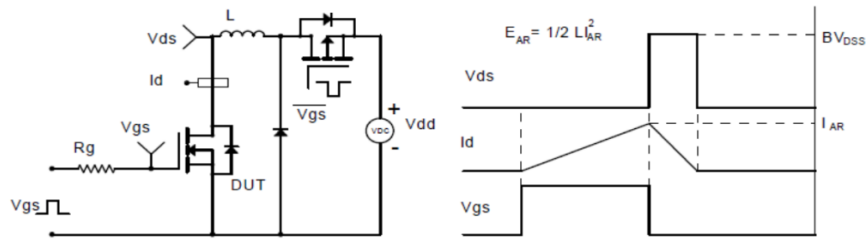


Land pattern
(Only for Reference)

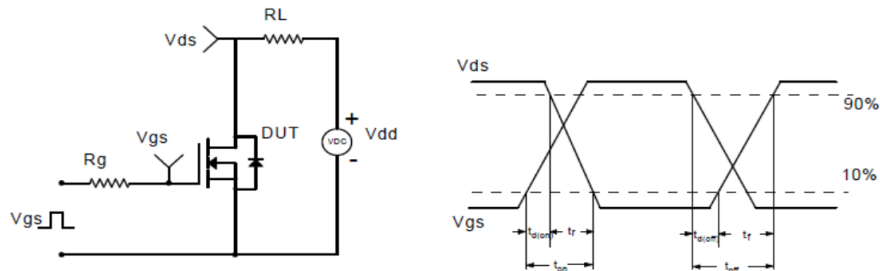
SYMBOL	MM			INCH			SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX		MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.75	0.80	0.028	0.030	0.031	E	2.90	3.00	3.10	0.114	0.118	0.122
A1	0.00	0.02	0.05	0.000	0.001	0.002	E1	0.89	0.99	1.09	0.035	0.039	0.043
A2	0.203REF			0.008REF			E2	0.42	0.52	0.62	0.017	0.020	0.024
b	0.35	0.40	0.45	0.014	0.016	0.018	K	0.35REF			0.014REF		
D	2.90	3.00	3.10	0.114	0.118	0.122	K2	0.25REF			0.010REF		
D1	2.30	2.40	2.50	0.091	0.094	0.098	L	0.22	0.32	0.42	0.009	0.013	0.017
e	0.65BSC			0.026BSC									

Note: Dimensions do not inclusive burrs and mold flash.

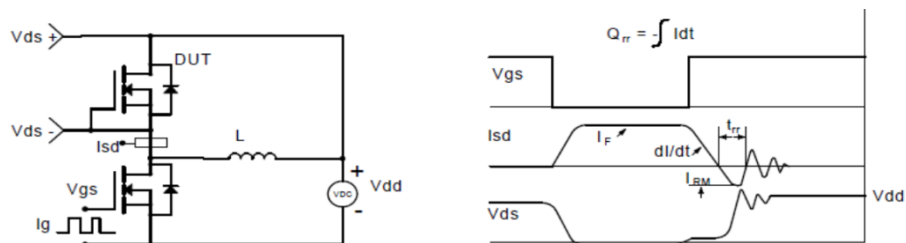
Avalanche Test Circuit and Waveforms



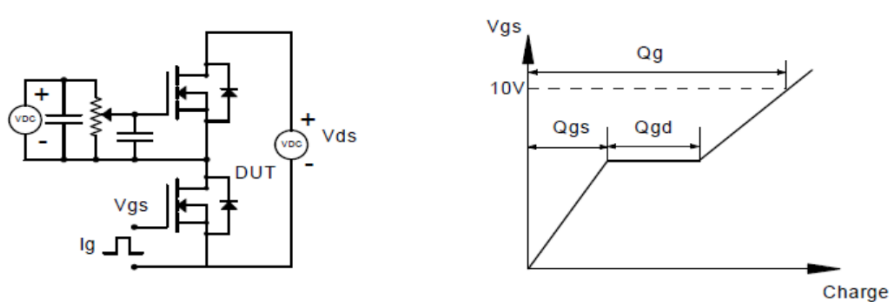
Switching Time Test Circuit and Waveforms



Diode Recovery Test Circuit and Waveforms



Gate Charge Test Circuit and Waveform



Customer Service

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